

Part Number: IB450S300



UHF Radar Transistor

The high power pulsed radar transistor device part number IB450S300 is designed for UHF radar systems operating at 450 MHz. While operating in class C mode this common base device supplies a minimum of 300 watts of peak pulse power under the conditions of 30 μ s pulse width and 10% duty cycle. All devices are 100% screened for large signal RF parameters. Excellent spectral stability into output mismatch over a broad input power range make it ideal for use in reliable high power solid state transmitters.



This device is designed to be used to drive 4 IB450s300 devices.

Silicon Bipolar

- Ultra-high f_T

Class C Operation

- High Efficiency

Common Base Configuration

- Single Power Supply

Gold Metal

- Maximum Reliability

Emitter Ballasting

- Optimum Thermal Distribution

Internal Impedance Matching

- Ease of Use
- Ultra-low Loss Design

BeO Package

- Unmatched Thermal Reliability

RF Test Fixture

- Matched to 50 Ω
- Long-term Correlation
- 100% Device RF Screening
- No External Tuning Allowed

TYPICAL DATA TYPICAL DATA TYPICAL DATA TYPICAL DATA

Device	IB450S300
Pulse	30us/10%
Vcc	40V
Fixture	ITI508
RF Test Bench	RFTB13

Lot/SN	F(MHZ)	Po pk	Pin pk	Ic pk	RL	Nc	G	Droop	VSWR-S 1.5:1	LMT 3:1
2099-5	450	300	20.8	11.8	25.0	63.6	11.6	0.10	s	p
2099-6	450	300	22.2	11.67	24.0	64.3	11.3	0.10	s	p

MAXIMUM RATINGS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Collector-Emitter Voltage	V_{CES}	--	80	V	$V_{BE}=0V$.
BD	Emitter-Base Voltage	V_{EBO}	--	3.5	V	--
BD	Storage Temperature Range	T_{STG}	-55	+150	°C	--
BD	Operating Junction Temperature Range	T_J	-55	+200	°C	--
Note	Screen 'BD' = parameter qualified By Design.					

THERMAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Thermal Resistance	$R_{TH(JC)}$	--	0.25	°C/W	$V_{CC}=V1$, $PW=PW1$, $DF=DF1$, $T_F=25\pm5^\circ C$, $P_{OUT}=300W$, $F=F1$.
Note	Screen 'BD' = parameter qualified By Design.					

PROCESSING SPECIFICATIONS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	DC Wafer Probe	--	--	--	--	Per Integra specification.
Q1	Wafer DC and RF Qualification	--	--	--	--	Per Integra specification.
LM	Wire Bond Strength	--	--	--	--	Line monitor per Integra specification.
100%	Pre-cap visual inspection	--	--	--	--	Per Integra specification.
100%	Gross leak test	--	--	--	--	MIL-STD-750D, Method 1071.6, Test Condition C.
Note	Screen 'Q1' = parameter is qualified by assembly and test of 3 pieces minimum per wafer.					
Note	Screen 'LM' = parameter is qualified by assembly line monitor.					

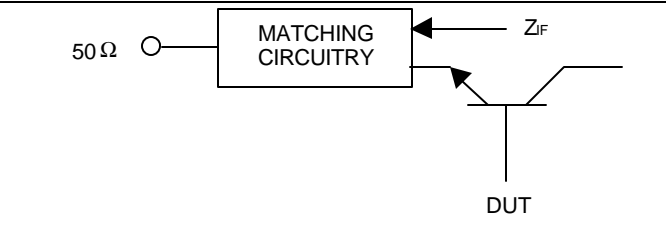
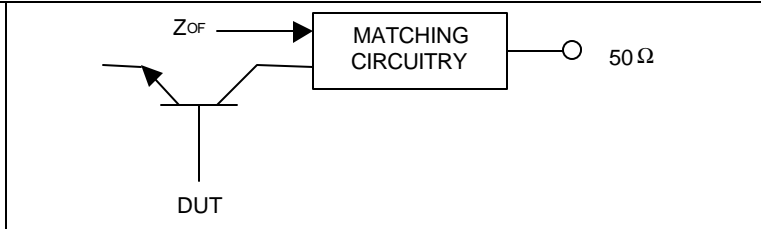
DC ELECTRICAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Collector-Emitter Breakdown Voltage	BV_{CES}	80	--	Vdc	$I_C=30mA$, $V_{BE}=0V$, $T_F=25\pm5^\circ C$.
100%	Zero Base Voltage Collector Leakage Current	I_{CES}	--	7.5	mA	$V_{CE}=40V$, $V_{BE}=0V$, $T_F=25\pm5^\circ C$.
100%	DC Current Gain	H_{FE}	20	90	--	$V_{CE}=5V$, $I_C=0.25A$, $T_F=25\pm5^\circ C$.

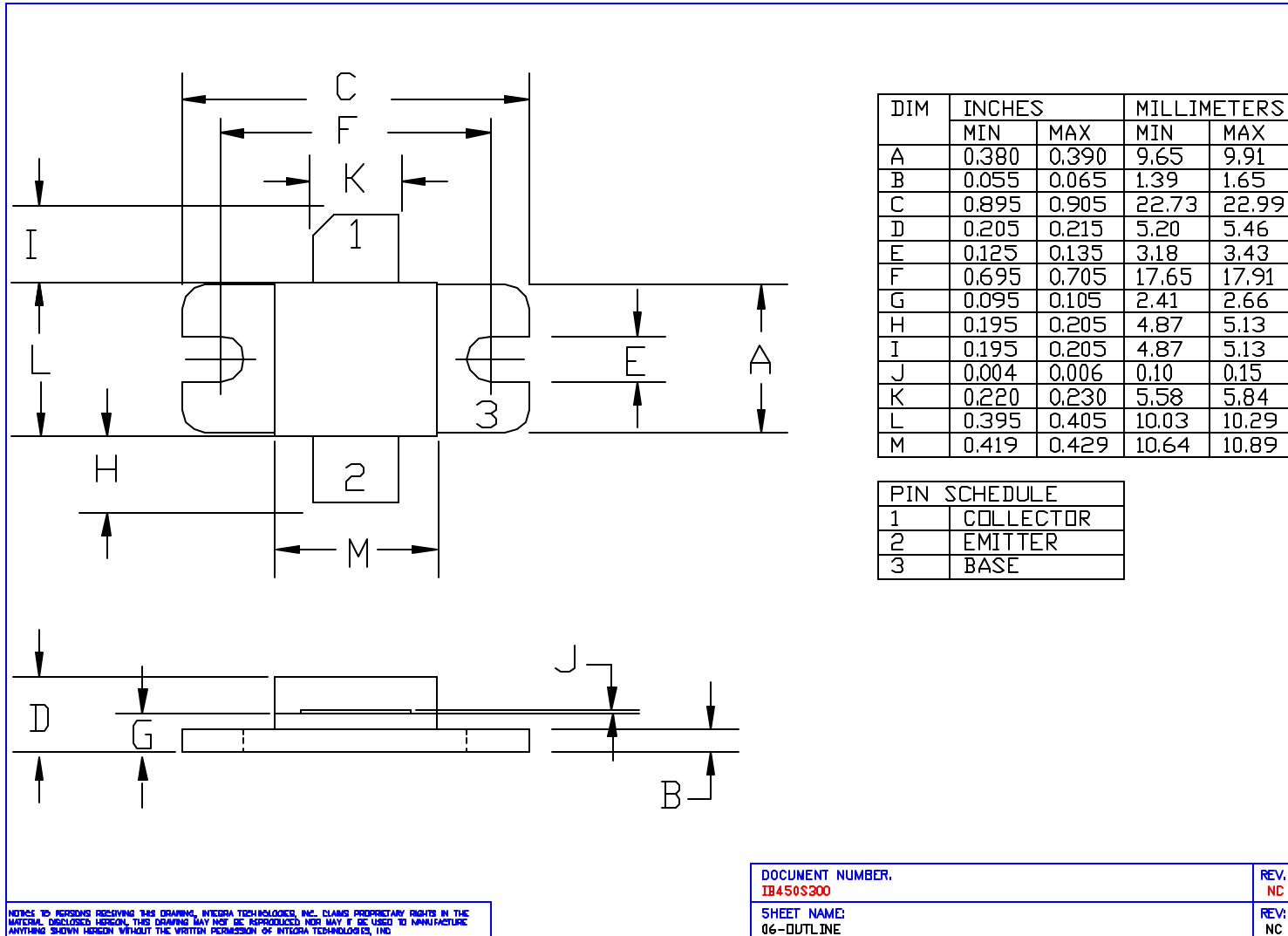
RF ELECTRICAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Input Return Loss	IRL	9	--	dB	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_{OUT}=P_{OUT1}, F=F1.$
100%	Power Gain	G_p	9.5	--	dB	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_{OUT}=P_{OUT1}, F=F1.$
100%	Collector Efficiency ($P_o/I_c/V_{CC}$)	N_c	50	--	%	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_{OUT}=P_{OUT1}, F=F1.$
100%	Pulse Amplitude Droop	D	--	0.5	dB	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_{OUT}=P_{OUT1}, F=F1.$
100%	Stability into 1.5:1 VSWR	VSWR-S	--	--	--	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_{OUT}=P_{OUT1}, F=F1.$ Rotate 1.5:1 output VSWR through 360° phase. No oscillatory or pulse break-up characteristics allowed on detected output pulse. All non-harmonically related signals must be at least -65 dBc.
100%	3:1 Load Mismatch Tolerance	LMT	--	--	--	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_{OUT}=P_{OUT1}, F=F1.$ Rotate 3:1 output VSWR through 360° phase. Post-test P_{OUT} = Pre-test $P_{OUT} \pm 10W$.
BD	Pulse Risetime	RT	--	180	ns	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_{OUT}=P_{OUT1}, P_{OUT2}, P_{OUT3}, F=F1, F2, F3.$ Measure between 10% and 90% detected power points.
Note	$V1 = 40V; PW1 = 30\mu s; DF1 = 10%; P_{OUT1} = 300W; F1 = 450 MHz.$					
Note	T_F = Device flange temperature.					
Note	Screen 'BD' = parameter qualified By Design.					

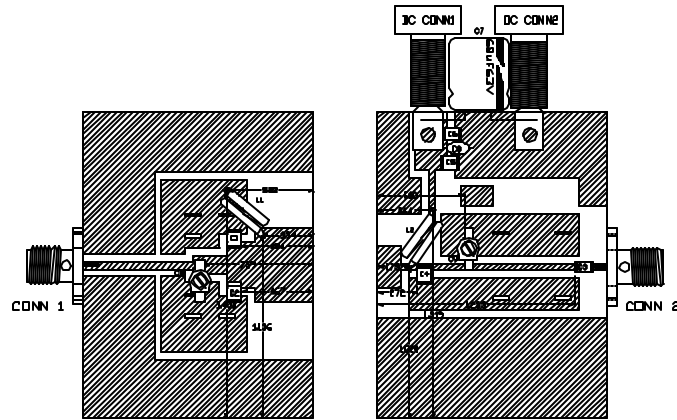
RF TEST FIXTURE IMPEDANCE CHARACTERISTICS

Frequency (MHz)	$Z_F (W)$	$Z_{OF} (W)$
450	1.27-j2.61	2.45-j0.980
Impedance Definition		

PACKAGE DIMENSIONAL OUTLINE DRAWING



RF TEST FIXTURE



COMPONENT	DESCRIPTION
TR1	TRANSISTOR 3DBE550, MOUNT HARD TO THE RIGHT
PC BOARD	INSULATED, 1/8" THICK
C1	CHIP CAPACITOR 22PF
C2	CHIP CAPACITOR 82PF
C3	CHIP CAPACITOR 470PF
C4	CHIP CAPACITOR 200PF
C5	CHIP CAPACITOR 470PF
C6	CHIP CAPACITOR 60PF
C7	ELCIBO LC CAPACITOR 60PF 63V
C8	ELCIBO LC CAPACITOR 51PF
C9	VARIABLE CHIP CAPACITOR 12 TO 30PF
C10	VARIABLE CHIP CAPACITOR 1.4 TO 60PF
L1	1/2 TURN, 90° VOLT
L2	1/2 TURN, 90° VOLT
DC CONN 1	BANANA JACK - BLACK
DC CONN 2	BANANA JACK - RED
TRANSISTOR CLAMP	NORCL CLAMP - 10
HEAT SINK	1/2 INCH HEATSINK - 11
INPUT PC BOARD BARRIER	1/4 INCH BRASS - 05
OUTPUT PC BOARD BARRIER	1/4 INCH BRASS - 05
NOTE	FIXTURE HARDWARE DRAWINGS AVAILABLE ON REQUEST

ASSEMBLY PARTS AND LIST

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DOCUMENT NUMBER: IB450S300	REV: NC
SHEET NAME 09-RF-TEST-FIXTURE-1- DF- 2	REV: NC

Part Number: IB450S300**Integra**
TECHNOLOGIES, INC.**DEFINITIONS**

Data Sheet Status	
Proposed Specification	This data sheet contains proposed specifications.
Preliminary Specification	This data sheet contains specifications based on preliminary measurements and data.
Product Specification	This data sheet contains final product specifications.
Maximum Ratings	
Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only and operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.	

WARNING

Product and environmental safety - toxic materials
This product contains beryllium oxide. The product is entirely safe provided that the BeO base is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with general or domestic waste.

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